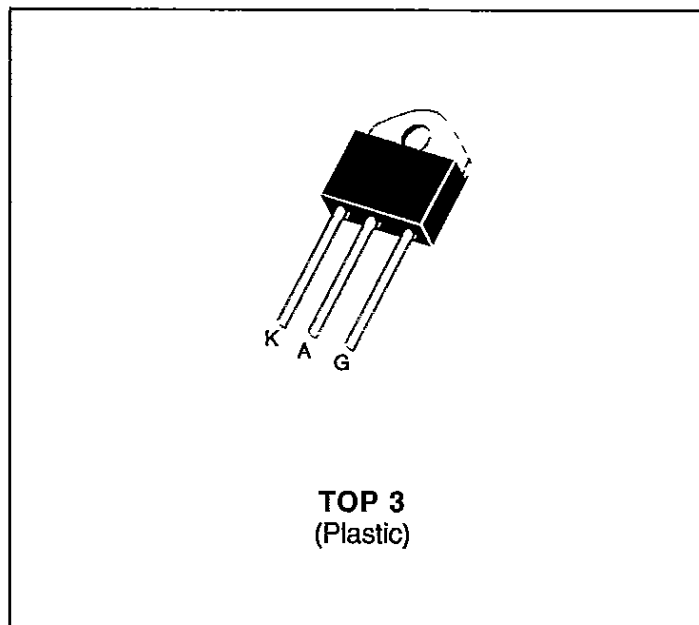




- GLASS PASSIVATED CHIP
- HIGH STABILITY AND RELIABILITY
- HIGH SURGE CAPABILITY
- HIGH ON-STATE CURRENT
- EASY MOUNTING ON HEATSINK



DESCRIPTION

General purpose SCR suited for power supplies up to 400 Hz on resistive or inductive loads.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		BTW69- 200N → 800N	BTW69- 1000N/1200N	Unit
$I_{T(RMS)}$	RMS on-state Current (1)	$T_c = 70^\circ C$	55		A
$I_{T(AV)}$	Mean on-state Current (1)	$T_c = 70^\circ C$	35		A
I_{TSM}	Non Repetitive Surge Peak on-state Current (T_j initial = $25^\circ C$) (2)	$t = 8.3$ ms	525	420	A
		$t = 10$ ms	500	400	
I^2t	I^2t Value for Fusing	$t = 10$ ms	1250	800	A^2s
di/dt	Critical Rate of Rise of on-state Current (3)		100		$A/\mu s$
T_{stg} T_j	Storage and Operating Junction Temperature Range		-40 to 125		$^\circ C$
			-40 to 125		$^\circ C$

Symbol	Parameter	BTW69-						Unit
		200N	400N	600N	800N	1000N	1200N	
V_{DRM} V_{RRM}	Repetitive Peak off-state Voltage (4)	200	400	600	800	1000	1200	V

(1) Single phase circuit, 180° conduction angle.

(2) Half sine wave.

(3) $I_G = 800$ mA $di/dt = 1$ A/ μs .

(4) $T_j = 125^\circ C$.

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction-case for D.C.	0.87	$^\circ C/W$
$R_{th(c-h)}$	Contact (case to heatsink)	0.20	$^\circ C/W$

GATE CHARACTERISTICS (maximum values)

T-25-17

$P_{GM} = 50 \text{ W}$ ($t_p = 10 \mu\text{s}$)

$I_{FGM} = 2 \text{ A}$ ($t_p = 10 \mu\text{s}$)

$V_{RGM} = 5 \text{ V}$

$P_{G(AV)} = 1 \text{ W}$

$V_{FGM} = 15 \text{ V}$ ($t_p = 10 \mu\text{s}$)

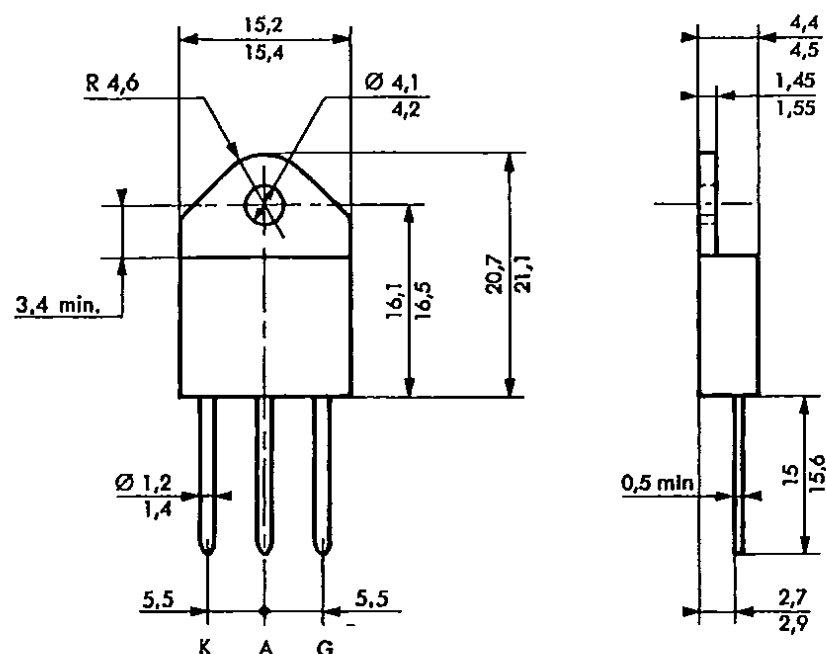
ELECTRICAL CHARACTERISTICS

SGS-THOMSON

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
I_{GT}	$T_J = 25^\circ\text{C}$ Pulse Duration $> 20 \mu\text{s}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$			80	mA
V_{GT}	$T_J = 25^\circ\text{C}$ Pulse Duration $> 20 \mu\text{s}$	$V_D = 12 \text{ V}$	$R_L = 33 \Omega$			1.5	V
V_{GD}	$T_J = 125^\circ\text{C}$	$V_D = V_{DRM}$	$R_L = 3.3 \text{ k}\Omega$	0.2			V
I_H	$T_J = 25^\circ\text{C}$	$I_T = 0.5 \text{ A}$	Gate Open		20	150	mA
I_L	$T_J = 25^\circ\text{C}$ Pulse Duration $> 20 \mu\text{s}$	$V_D = 12 \text{ V}$	$I_G = 160 \text{ mA}$		40		mA
V_{TM}	$T_J = 25^\circ\text{C}$	$I_{TM} = 110 \text{ A}$	$t_p = 10 \text{ ms}$			2	V
I_{DRM}	V_{DRM} Specified		$T_J = 25^\circ\text{C}$			0.02	mA
			$T_J = 125^\circ\text{C}$			6	
I_{RRM}	V_{RRM} Specified		$T_J = 25^\circ\text{C}$			0.02	mA
			$T_J = 125^\circ\text{C}$			6	
t_{gt}	$T_J = 25^\circ\text{C}$ $I_G = 200 \text{ mA}$	$V_D = V_{DRM}$ $di_G/dt = 0.2 \text{ A}/\mu\text{s}$	$I_T = 110 \text{ A}$		2		μs
t_q	$T_J = 125^\circ\text{C}$ $V_D = 67\% V_{DRM}$ Gate Open	$I_T = 110 \text{ A}$ $di/dt = 30 \text{ A}/\mu\text{s}$	$V_R = 75 \text{ V}$ $dv/dt = 20 \text{ V}/\mu\text{s}$		100		μs
dv/dt^*	$T_J = 125^\circ\text{C}$ Gate Open Linear Slope up to $V_D = 67\% V_{DRM}$		$V_{DRM} \leq 800 \text{ V}$	500			V/ μs
			$V_{DRM} \geq 1000 \text{ V}$	250			

* For higher guaranteed values, please consult us.

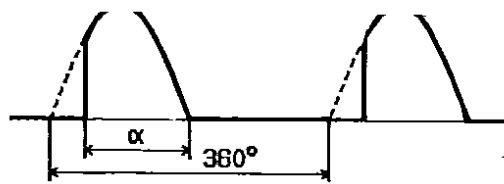
PACKAGE MECHANICAL DATA : TOP 3 Plastic



Cooling method : by conduction (method C)

Marking : type number

Weight : 5 g.



T-25-17

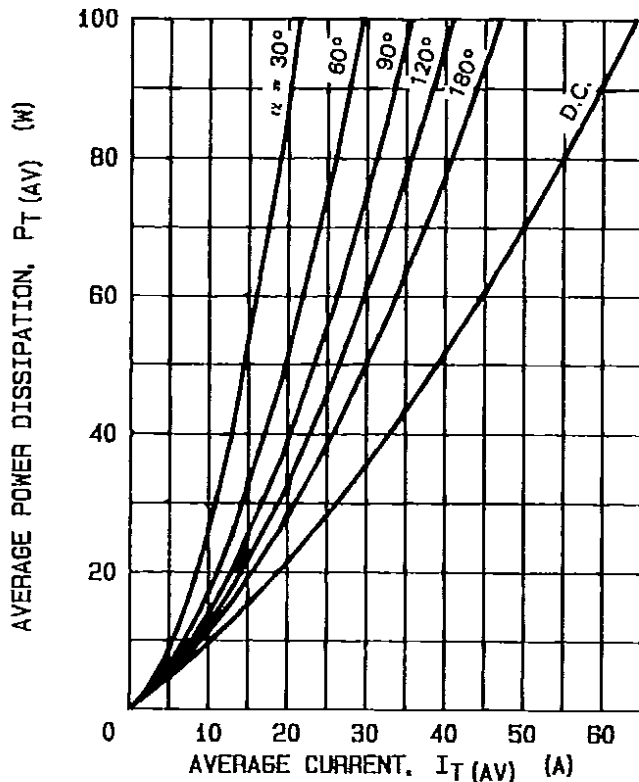


FIG.1 - MAXIMUM ON-STATE POWER DISSIPATION FOR SINUSOIDAL CURRENT WAVEFORM

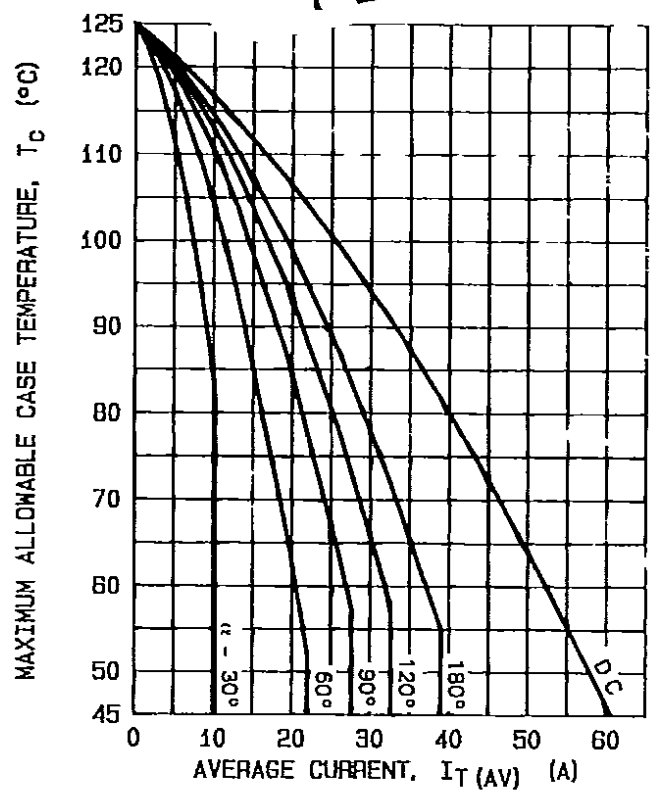


FIG.2 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR SINUSOIDAL CURRENT WAVEFORM

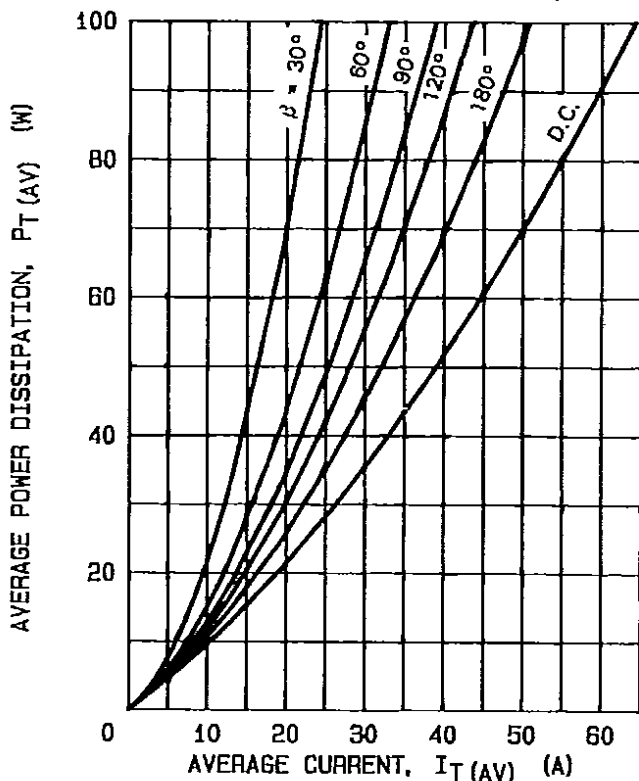
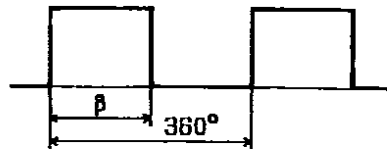


FIG.3 - MAXIMUM ON-STATE POWER DISSIPATION FOR RECTANGULAR CURRENT WAVEFORM

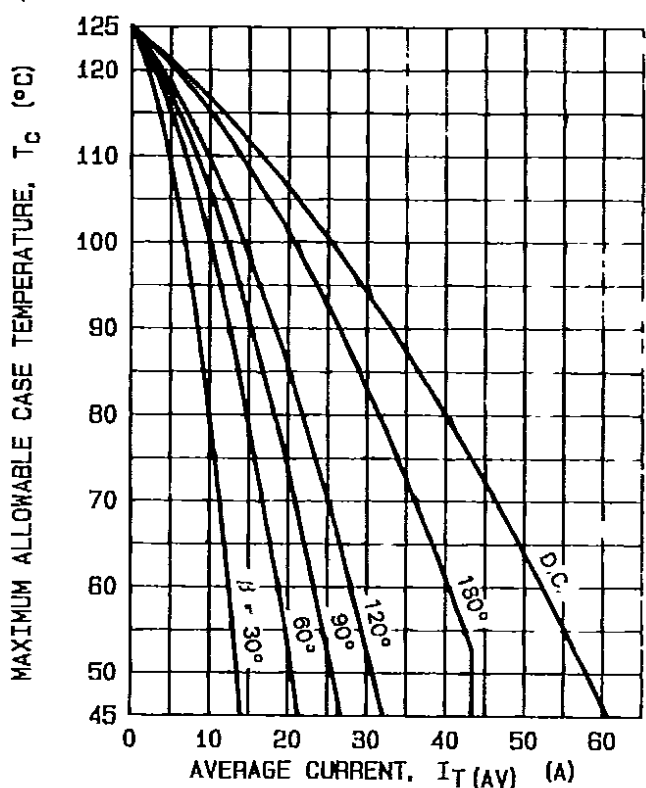


FIG.4 - MAXIMUM ALLOWABLE CASE TEMPERATURE FOR RECTANGULAR CURRENT WAVEFORM

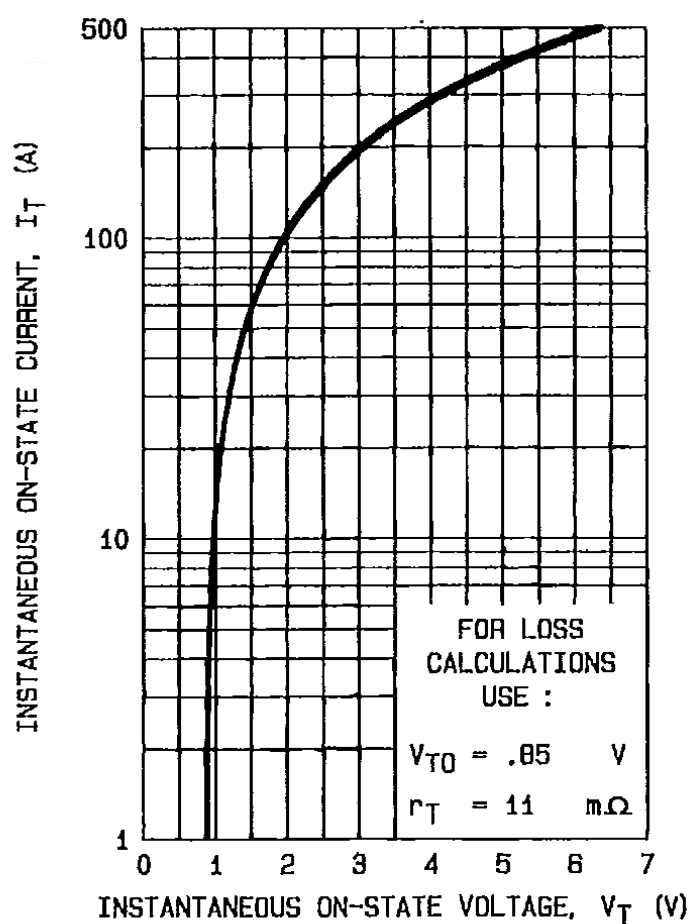


FIG.5 - MAXIMUM ON-STATE CONDUCTION CHARACTERISTIC ($T_J = 125^\circ\text{C}$).

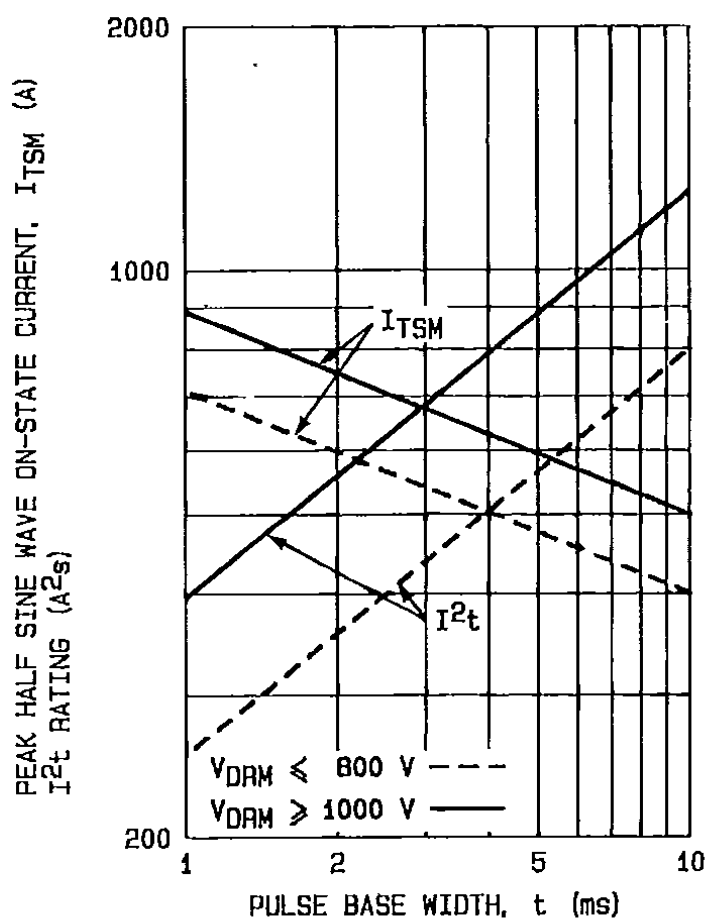


FIG.6 - NON REPETITIVE SUB-CYCLE SURGE ON-STATE CURRENT AND I^2t RATING (INITIAL $T_J = 25^\circ\text{C}$).

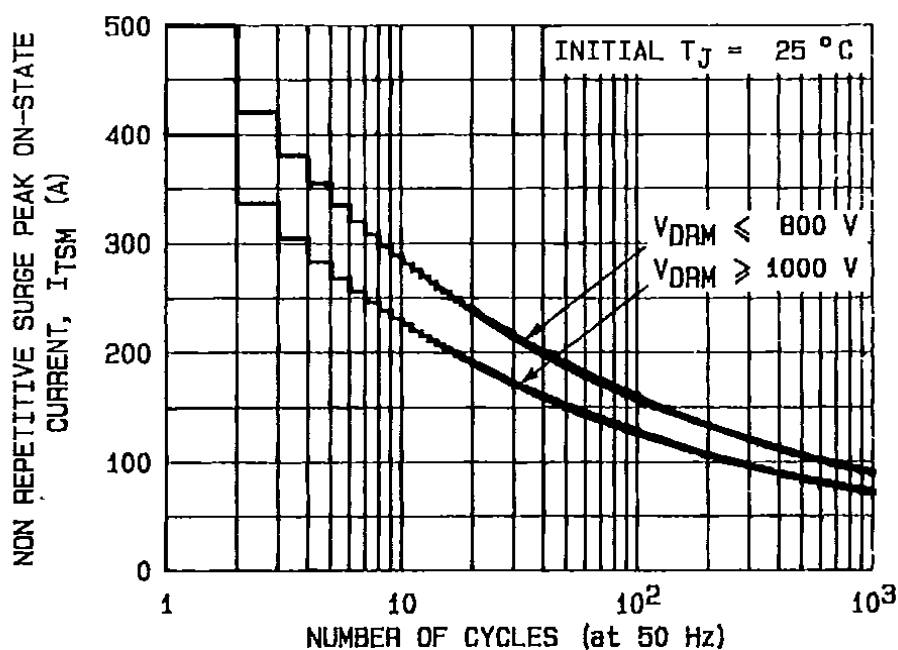


FIG.7 - NON REPETITIVE SURGE PEAK ON-STATE CURRENT VERSUS NUMBER OF CYCLES.